MOSFETs Silicon N-Channel MOS (π-MOSⅧ)

# TK5A90E

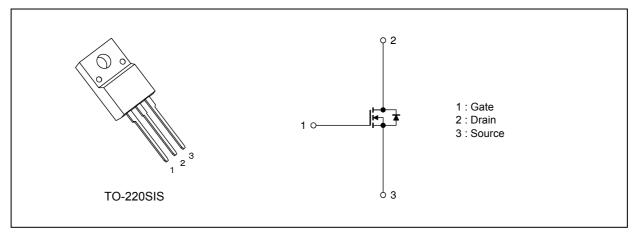
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance :  $R_{DS(ON)} = 2.5 \Omega$  (typ.)
- (2) Low leakage current :  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 720 \ V)$
- (3) Enhancement mode :  $V_{th}$  = 2.5 to 4.0 V (V\_{DS} = 10 V,  $I_{D}$  = 0.45 mA)

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) ( $T_a = 25 \,^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	900	V
Gate-source voltage		V <sub>GSS</sub>	±30	1
Drain current (DC)	(Note 1)	I <sub>D</sub>	4.5	A
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	13.5	1
Power dissipation (T <sub>c</sub> :	= 25 °C)	PD	40	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	202	mJ
Avalanche current		I <sub>AR</sub>	4.5	A
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	4.5	1
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	13.5	1
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	1
Isolation voltage (RMS) (t =	= 1.0 s)	V <sub>ISO(RMS)</sub>	2000	V
Mounting torque		TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

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#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit	
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	3.125	°C/W	
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	62.5		

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V<sub>DD</sub> = 90 V, T<sub>ch</sub> = 25 °C (initial), L = 18.3 mH, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 4.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

### 6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V	_	—	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	900	—	_	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.45 mA	2.5	_	4.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.3 A		2.5	3.1	Ω

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,	_	950	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz		8	_	
Output capacitance	C <sub>oss</sub>		_	75	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz	_	4.0	—	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig.6.2.1	_	25	—	ns
Switching time (turn-on time)	t <sub>on</sub>		_	55	_	
Switching time (fall time)	t <sub>f</sub>			15	_	
Switching time (turn-off time)	t <sub>off</sub>			80	_	
MOSFET dv/dt ruggedness	dv/dt	$V_{DD}$ = 0 to 400 V, I <sub>D</sub> = 4.5 A	15	_	_	V/ns

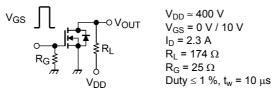


Fig. 6.2.1 Switching Time Test Circuit

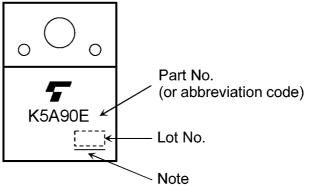
### 6.3. Gate Charge Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V,	_	20		nC
Gate-source charge 1	Q <sub>gs1</sub>	I <sub>D</sub> = 4.5 A	_	7	_	
Gate-drain charge	Q <sub>gd</sub>			10	_	

### 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 4.5 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 4.5 A, V <sub>GS</sub> = 0 V,	_	1000	—	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 100 A/μs	_	6.5	—	μC
Peak reverse recovery current	l <sub>rr</sub>			18		А

### 7. Marking (Note)

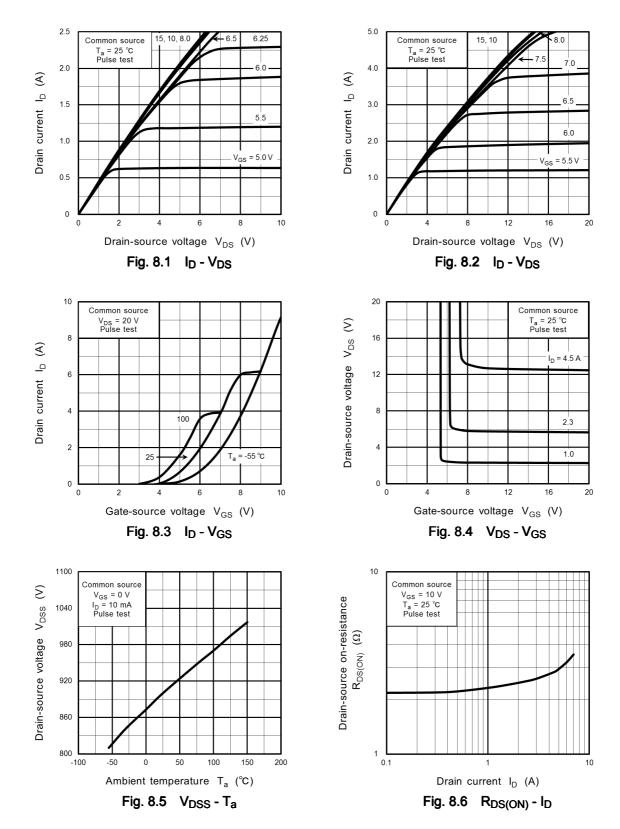


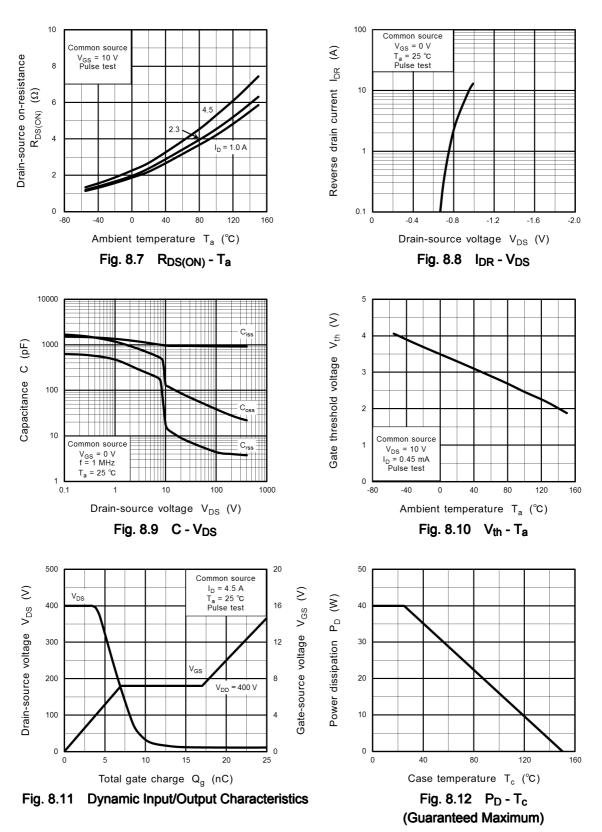


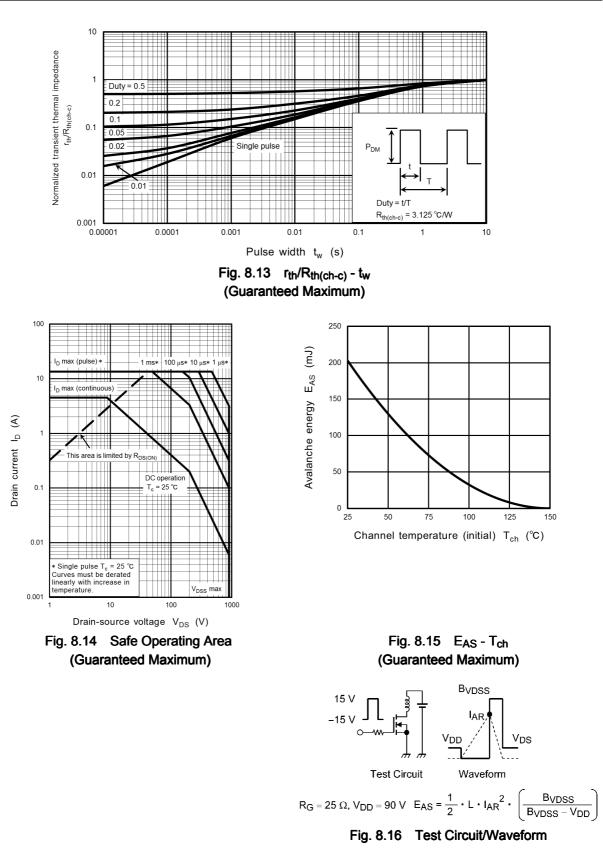
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### 8. Characteristics Curves (Note)



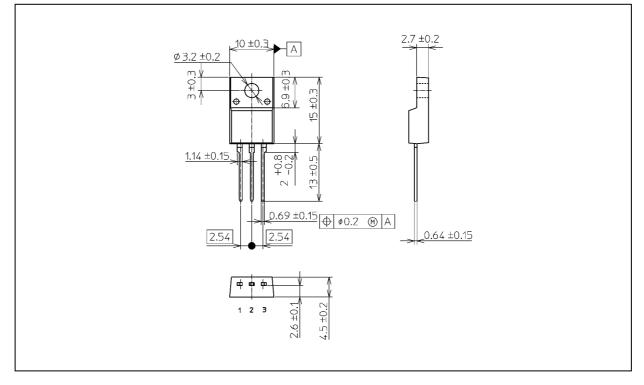




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### Package Dimensions

Unit: mm



#### Weight: 1.7 g (typ.)

Package Name(s)		
TOSHIBA: 2-10U1S		
Nickname: TO-220SIS		

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